40V PNP SMALL SIGNAL TRANSISTOR IN X1-DFN1006-3

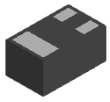
Features

- BV_{CEO} > -40V
- I_C = -200mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 Times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DIODES™ MMBT3904LP
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

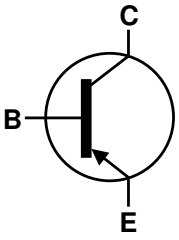
Mechanical Data

- Package: X1-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu, Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0008 grams (Approximate)

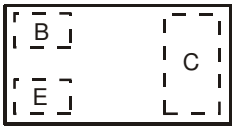
X1-DFN1006-3



Bottom View



Device Symbol



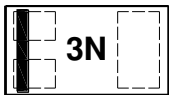
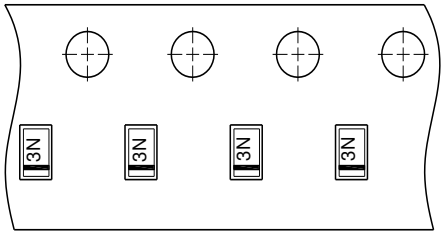
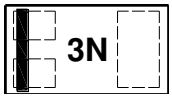
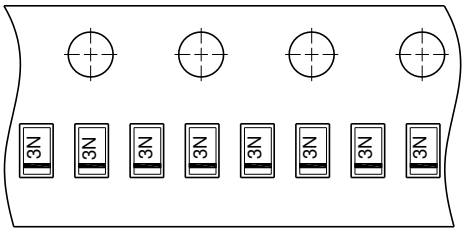
Top View
Device Schematic

Ordering Information (Note 4)

Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
					Qty.	Carrier
MMBT3906LP-7	X1-DFN1006-3	3N	7	8	3,000	Reel
MMBT3906LP-7B	X1-DFN1006-3	3N	7	8	10,000	Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

MMBT3906LP-7	 3N = Product Type Marking Code Top View Bar Denotes Base and Emitter Side 
MMBT3906LP-7B	 3N = Product Type Marking Code Top View Bar Denotes Base and Emitter Side 

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-200	mA
Peak Collector Current	I_{CM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	400	mW
	(Note 6)		1000	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	310	°C/W
	(Note 6)		120	
Thermal Resistance, Junction to Case	(Note 5)	$R_{\theta JC}$	60	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

Notes:
5. For the device mounted on minimum recommended pad layout 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition.
6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics

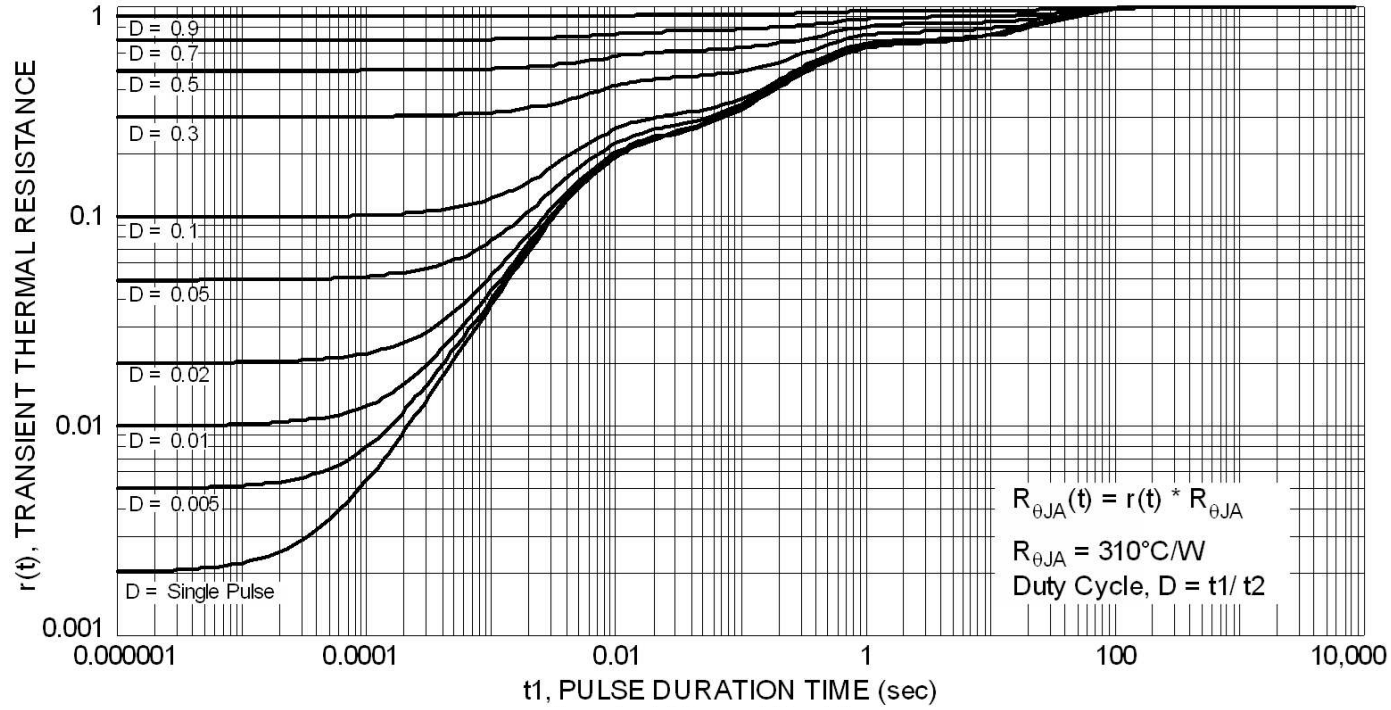


Fig. 1 Transient Thermal Resistance

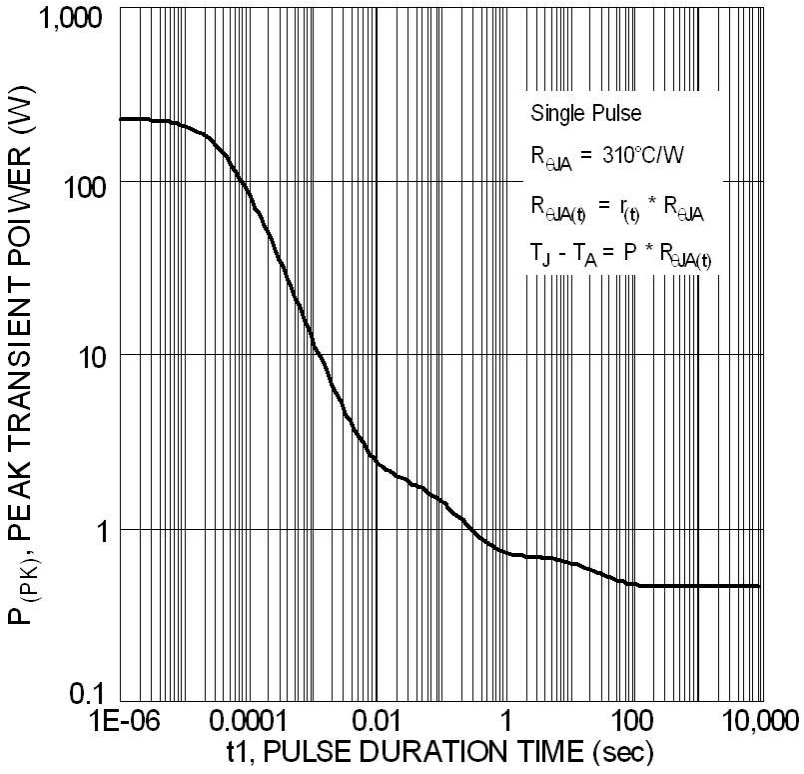


Fig. 2 Single Pulse Maximum Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	I_C = -100µA
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	-40	—	V	I_C = -10.0mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	—	V	I_E = -100µA
Collector Cutoff Current	I_{CEX}	—	-50	nA	V_{CE} = -30V, $V_{EB(off)}$ = -3.0V
	I_{CBO}	—	-50	nA	V_{CB} = -30V
Base Cutoff Current	I_{BL}	—	-50	nA	V_{CE} = -30V, $V_{EB(off)}$ = -3.0V
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h_{FE}	60	—	—	I_C = -100µA, V_{CE} = -1.0V
		80	—		I_C = -1.0mA, V_{CE} = -1.0V
		100	300		I_C = -10mA, V_{CE} = -1.0V
		60	—		I_C = -50mA, V_{CE} = -1.0V
		30	—		I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-0.25	V	I_C = -10mA, I_B = -1.0mA
		—	-0.40		I_C = -50mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65	-0.85	V	I_C = -10mA, I_B = -1.0mA
		—	-0.95		I_C = -50mA, I_B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.5	pF	V_{CB} = -5.0V, f = 1.0MHz
Input Capacitance	C_{ibo}	—	10	pF	V_{EB} = -0.5V, f = 1.0MHz
Input Impedance	h_{ie}	2	12	kΩ	V_{CE} = -10V, I_C = -1.0mA f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	10	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	3	60	µS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = -20V, I_C = -10mA f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = -3.0V, I_C = -10mA I_{B1} = -I_{B2} = -1.0mA
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	225	ns	
Fall Time	t_f	—	75	ns	

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

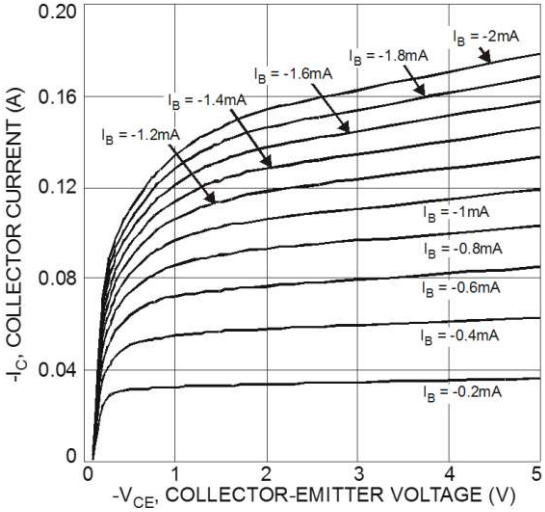


Fig. 3 Typical Collector Current vs. Collector-Emitter Voltage

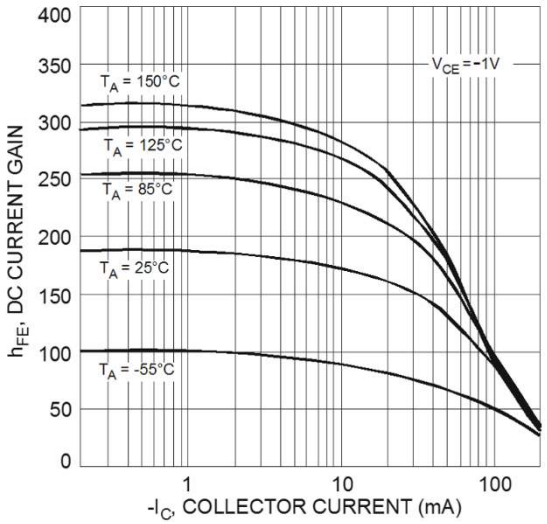


Fig. 4 Typical DC Current vs. Collector Current

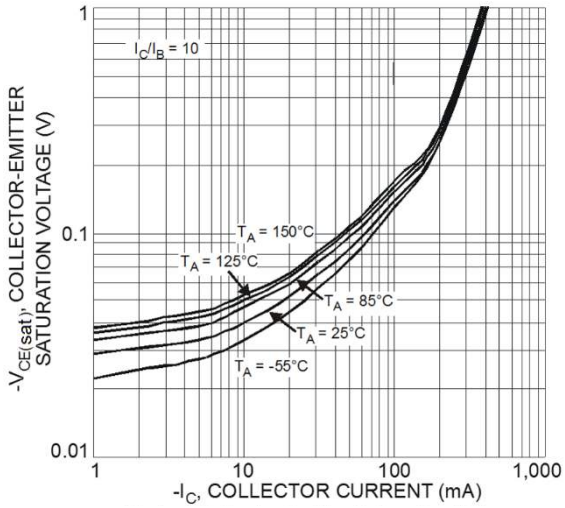


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

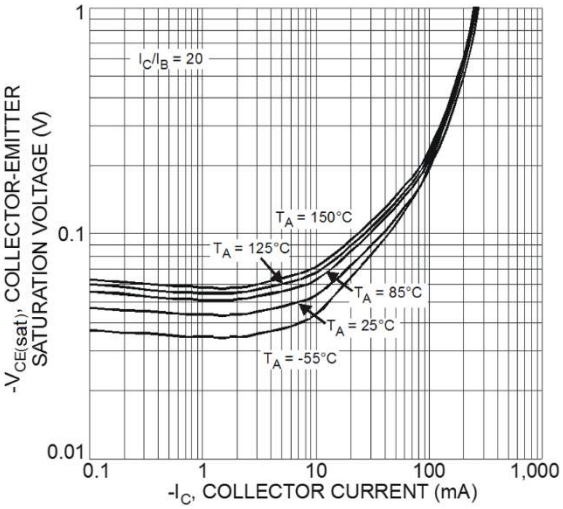


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

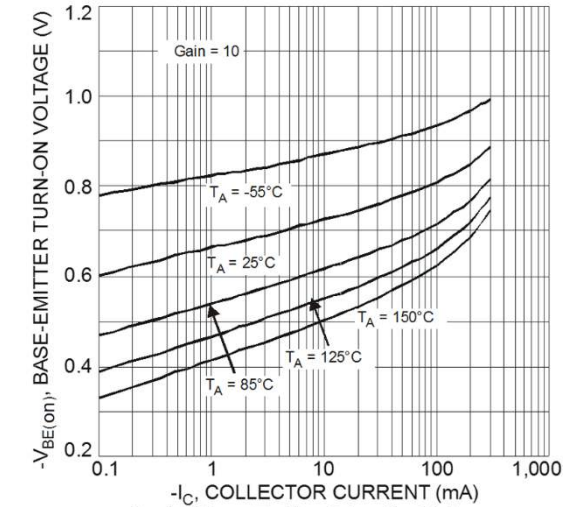


Fig. 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

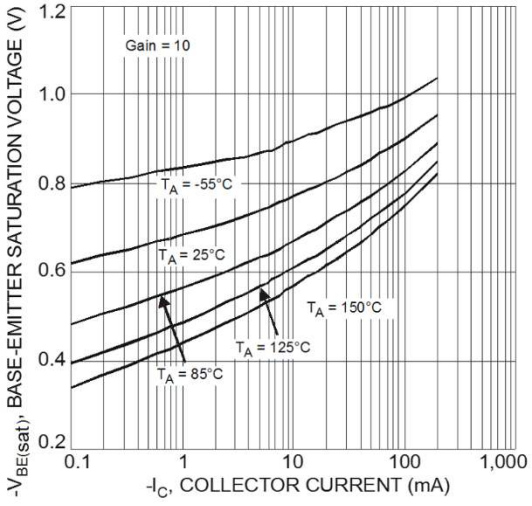
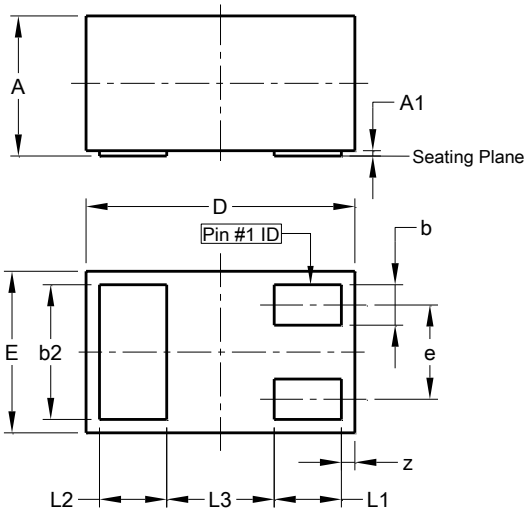


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3

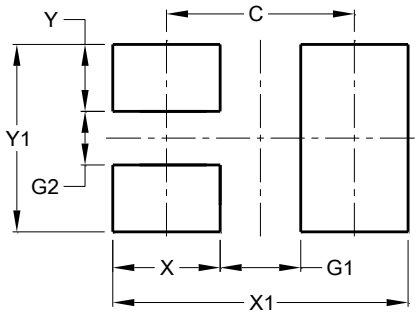


X1-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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